

ABSTRACT OF THE DISCLOSURE

With a microwave FET, an incorporated Schottky junction capacitance or PN junction capacitance is small and such a junction is weak against static electricity. However, with a microwave device, the method of connecting a protecting diode cannot be used since this method increases the parasitic capacitance and causes degradation of the high-frequency characteristics. In order to solve the above problems, a protecting element, having a first n^+ -type region – insulating region – second n^+ -type region arrangement is connected in parallel between two terminals of a protected element having a PN junction, Schottky junction, or capacitor. Since discharge can be performed between the first and second n^+ regions that are adjacent each other, electrostatic energy that would reach the operating region of an FET can be attenuated without increasing the parasitic capacitance.